Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S4	22	semix.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 08:56
S6	9	SEMIX adj Incorporated.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 08:57
S7	9	(SEMIX adj Incorporated).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 08:59
S8	152	EBR and spin and apparatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:00
S9	3825	spin near coat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:15
S10	1021	EBR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:00
S11	101	backside near rinse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:15
S12	1	S9 and S10 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:03
S15	4344066	apparatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:03
S16	7	two near nozzel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:12

S18	1	"10/826487"	US-PGPUB; USPAT;	OR	ON	2006/02/14 09:12
			EPO; JPO; DERWENT; IBM_TDB	• ! ! !		
S19	13835	two near nozzle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:13
S20	38	S9 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:14
S22	413	backside same rinse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:15
S24	24	S9 and S15 and (EBR or (edge adj bead adj removal))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:23
S26	19	S24 and nozzle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:19
S27	10	S24 and (two near nozzle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:20
S28	9	S24 and (three near nozzle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:23
S29	600	water and (EBR or (edge adj bead adj removal))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 09:23
S30	4	(dispense near water) and (EBR or (edge adj bead adj removal))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:37

S31 ·	3868	water and simultaneous and etch	US-PGPUB; USPAT;	OR	ON	2006/02/14 10:03
:		- - - - -	EPO; JPO; DERWENT; IBM_TDB		; ; ;	
S33	380	S31 and dispense	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:04
S34	218	S33 and nozzle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:04
S35	72	S34 and etchant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:04
S37	6403	protect near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:37
S38	8437	DI adj water	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:37
S40	3	S37 same S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:38
S41	98	S37 and S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:40
S44	60	(water) near protectant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:47
S45	4	S44 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:42

S50	270865	sulfuric	US-PGPUB; USPAT;	OR	ON	2006/02/14 10:48
:	1		EPO; JPO; DERWENT; IBM_TDB		•	· ·
+ S51	1323	EBR or (edge adj bead adj removal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:48
S52	248054	hydrochloric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:49
S53	128053	S50 and S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 10:49
S54	44	S51 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:02
S55	75	(water) near passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:53
S56	21	S55 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:55
S58	221	(water) near (pre adj treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:54
S62	537	prepare near surface same water	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:54
S63	1622044	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:55

S64	34	S58 and S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 12:55
S65	87	S62 and S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	i	ON	2006/02/14 12:55
S66	5333662	"1" near fluid near drop near three near seconds to about S55 fluid drop every "second."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:03
S68	1	about near "1" near fluid near drop near every near second	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:03
S69	86	"1" near drop near second	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:04
S70	41	S69 same (DI or water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:06
S71	14	(EBR and apparatus).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:12
S72	0	SOB and EBR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:11
S73	3786495	G	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:11
S74	37	SOG and EBR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:14

S76	2	(resist and spin and EBR).ab.	US-PGPUB; USPAT;	OR	ON	2006/02/14 14:15
			EPO; JPO; DERWENT; IBM_TDB	· ·	:	
S77 ·	80	((resist and spin and EBR) and apparatus)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON ;	2006/02/14 14:16
S78	14	(resist and spin and EBR) and (apparatus).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:17
S79	50	(edge adj bead adj removal).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:29
S80	4	S79 and drop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:20
S81	75	(edge adj bead adj removal) and drop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:26
S82	400	(edge adj bead adj removal) and (drops per second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:28
S83	397371	"1" near (drops per second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:28
S84	49	S82 and S83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:27
S85	1	(edge adj bead adj removal) and (drops adj per adj second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:28

S86	451196	(flow adj rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2006/02/14 14:45
S87	474	(edge adj bead adj removal)	IBM_TDB US-PGPUB; USPAT; EPO; JPO;	OR	ON	2006/02/14 14:45
! ! !			DERWENT; IBM_TDB			
S88	135	S86 and S87	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:29
S89	0	program near S87	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:45
S90	44	TEI and SOG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:45
S91	1	S90 and S87	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:48
S92	0	HCL near EBR and MI/min	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:48
S93	0	HCL near EBR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:48
S94	1	HCL same EBR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:48
S95	65	HCL and EBR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 14:48

S96	3	S95 and ml/min	US-PGPUB; USPAT;	OR	ON	2006/02/14 15:08
			EPO; JPO; DERWENT; IBM_TDB			
S97	48	(pulsing near water) and clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON :	2006/02/14 15:09
S98 :	6	S97 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:09
S99	68	(pulsed near water) and clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:10
S10 0	7	S99 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:13
S10 1	0	sccm near (DI adj water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:14
S10 2	28	sccm same (DI adj water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:21
S10 3	2	"6793836".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:30
S10 4	2	puddle near etch near solution	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:31
S10 5	5	puddle near etchant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:31

S10 6	450	water near puddle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	:	ON	2006/02/14 15:31
S10 7	6	S106 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:33
S10 8	195	wafer near scrub	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:34
S10 9	66	S108 and Di	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:34